

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD1729

DESCRIPTION

- With TO-3PN package
- Built-in damper diode
- High voltage ,high speed
- Wide area of safe operation

APPLICATIONS

- For horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

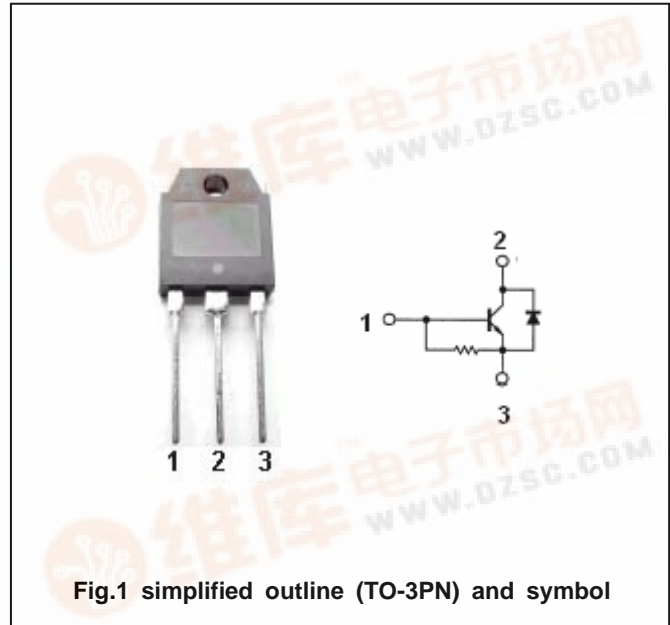


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	700	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current (DC)		3.5	A
I _{CM}	Collector current (Pulse)		10	A
I _B	Base current		1.5	A
P _C	Collector power dissipation	T _C =25°C	60	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =500mA; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A; I _B =0.8A			8.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =3A; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =750V; I _E =0			10	μA
		V _{CB} =1500V; I _E =0			1	mA
h _{FE}	DC current gain	I _C =0.5A ; V _{CE} =5V	5		25	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		2		MHz
V _F	Diode forward voltage	I _F =-3.5A, I _B =0			2.0	V

Switching times

t _s	Storage time	I _C =3A; I _{B1} =0.8A I _{B2} =-1.6A V _{CC} =200V		1.5		μs
t _f	Fall time			0.2		μs

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PACKAGE OUTLINE

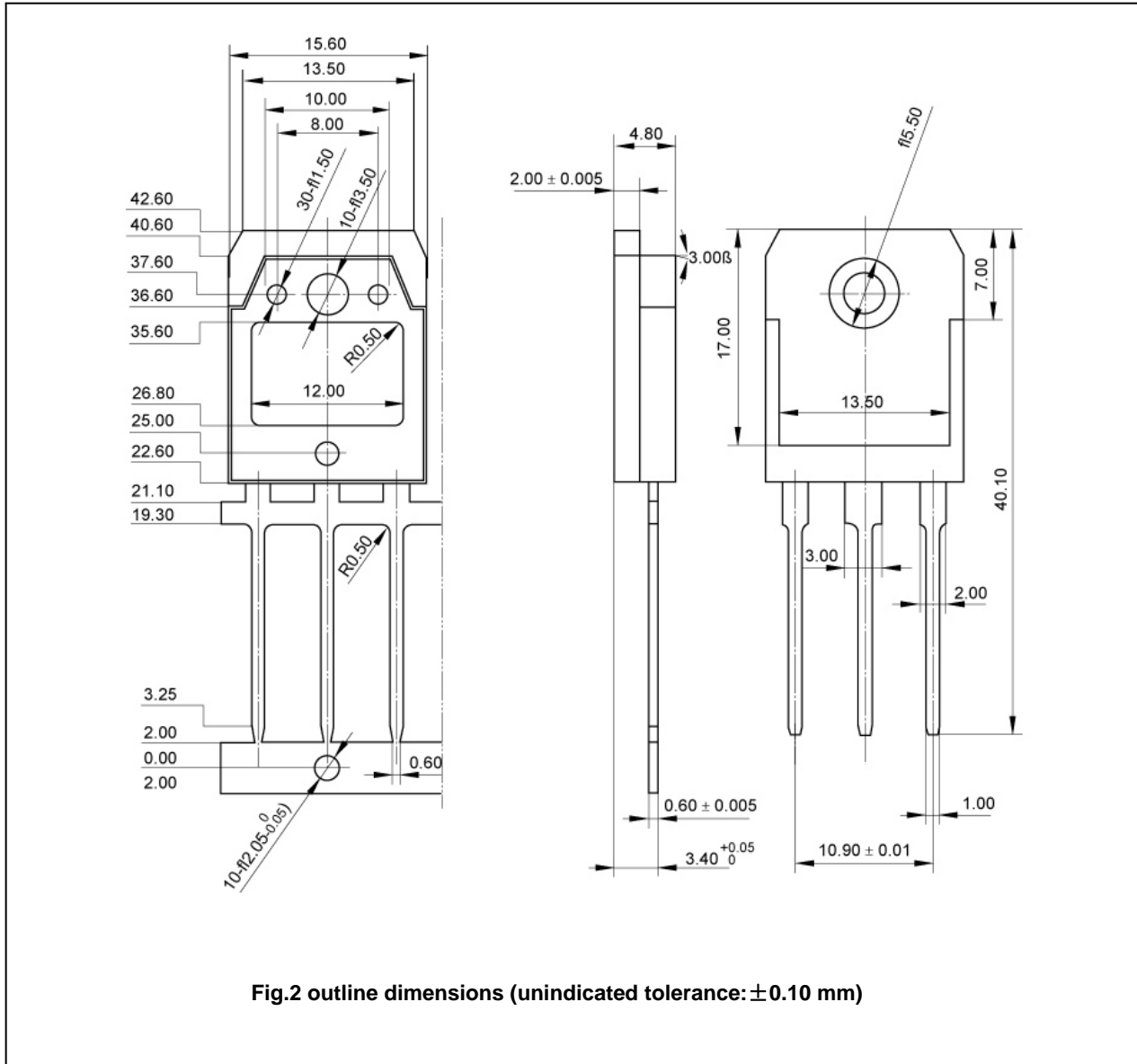


Fig.2 outline dimensions (unindicated tolerance: ±0.10 mm)